TENTATIVE TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

524,288-WORD BY 8-BIT STATIC RAM

DESCRIPTION

The TC55NEM208AFPN/AFTN is a 4,194,304-bit static random access memory (SRAM) organized as 524,288 words by 8 bits. Fabricated using Toshiba's CMOS Silicon gate process technology, this device operates from a single 5V ± 10% power supply. Advanced circuit technology provides both high speed and low power at an operating current of 3 mA/MHz (typ) and a minimum cycle time of 55 ns. It is automatically placed in low-power mode at 1 μA standby current (typ) when chip enable ($\overline{CE}$) is asserted high. There are two control inputs. $\overline{CE}$ is used to select the device and for data retention control, and output enable ($\overline{OE}$) provides fast memory access. This device is well suited to various microprocessor system applications where high speed, low power and battery backup are required. And, with a guaranteed operating range of −40° to 85°C, the TC55NEM208AFPN/AFTN can be used in environments exhibiting extreme temperature conditions. The TC55NEM208AFPN/AFTN is available in a standard plastic 32-pin small-outline package (SOP) and normal and reverse pinout plastic 32-pin thin-small-outline package (TSOP).

FEATURES

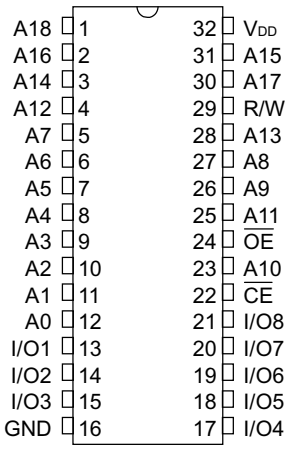
- Low-power dissipation
  Operating: 15 mW/MHz (typical)
- Single power supply voltage of 5 V ± 10%
- Power down features using $\overline{CE}$.
- Data retention supply voltage of 2.0 to 5.5 V
- Direct TTL compatibility for all inputs and outputs
- Wide operating temperature range of −40° to 85°C
- Standby Current (maximum):20 μA
- Access Times (maximum):

	TC55NEM208AFPN/AFTN	
	55	70
Access Time	55 ns	70 ns
$\overline{CE}$ Access Time	55 ns	70 ns
$\overline{OE}$ Access Time	30 ns	35 ns

- Package:
  SOP32-P-525-1.27 (AFPN) (Weight: g typ)
  TSOP II32-P-400-1.27 (AFTN) (Weight: g typ)

PIN ASSIGNMENT (TOP VIEW)

32 PIN SOP & TSOP

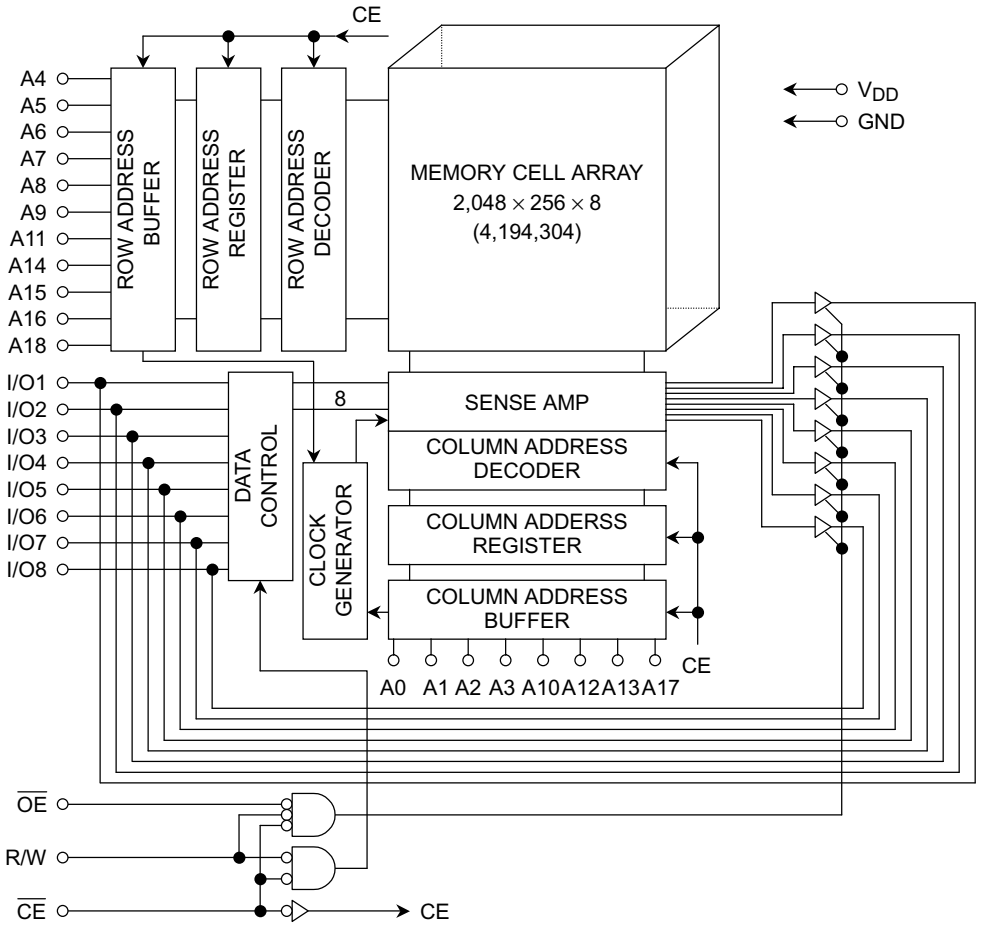


(AFPN/AFTN)

PIN NAMES

A0~A18	Address Inputs
R/W	Read/Write Control
$\overline{OE}$	Output Enable
$\overline{CE}$	Chip Enable
I/O1~I/O8	Data Inputs/Outputs
V_{DD}	Power (+5 V)
GND	Ground

BLOCK DIAGRAM



OPERATING MODE

MODE	$\overline{CE}$	$\overline{OE}$	R/W	I/O1~I/O8	POWER
Read	L	L	H	Output	I_{DDO}
Write	L	*	L	Input	I_{DDO}
Output Deselect	L	H	H	High-Z	I_{DDO}
Standby	H	*	*	High-Z	I_{DDS}

* = don't care
H = logic high
L = logic low

MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V_{DD}	Power Supply Voltage	−0.3~7.0	V
V_{IN}	Input Voltage	−0.3*~7.0	V
$V_{I/O}$	Input/Output Voltage	−0.5~V_{DD} + 0.5	V
P_D	Power Dissipation	0.6	W
T_{solder}	Soldering Temperature (10s)	260	°C
T_{stg}	Storage Temperature	−55~150	°C
T_{opr}	Operating Temperature	−40~85	°C

*: −2.0 V when measured at a pulse width of 20ns

DC RECOMMENDED OPERATING CONDITIONS (Ta = –40° to 85°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V_{DD}	Power Supply Voltage	4.5	5.0	5.5	V
V_{IH}	Input High Voltage	2.2	—	V_{DD} + 0.3	V
V_{IL}	Input Low Voltage	–0.3*	—	0.6	V
V_{DH}	Data Retention Supply Voltage	2.0	—	5.5	V

*: –2.0 V when measured at a pulse width of 20 ns

DC CHARACTERISTICS (Ta = –40° to 85°C, V_{DD} = 5 V ± 10%)

SYMBOL	PARAMETER	TEST CONDITION			MIN	TYP	MAX	UNIT
I_{IL}	Input Leakage Current	V_{IN} = 0 V~V_{DD}			—	—	±1.0	μA
I_{OH}	Output High Current	V_{OH} = 2.4 V			–1.0	—	—	mA
I_{OL}	Output Low Current	V_{OL} = 0.4 V			2.1	—	—	mA
I_{LO}	Output Leakage Current	$\overline{CE}$ = V_{IH} or R/W = V_{IL} or $\overline{OE}$ = V_{IH}, V_{OUT} = 0 V~V_{DD}			—	—	±1.0	μA
I_{DDO1}	Operating Current	$\overline{CE}$ = V_{IL} and R/W = V_{IH}, I_{OUT} = 0 mA, Other Input = V_{IH}/V_{IL}	t_{cycle}	MIN	—	—	35	mA
				1 μs	—	8	—	
I_{DDO2}		$\overline{CE}$ = 0.2 V and R/W = V_{DD} – 0.2 V, I_{OUT} = 0 mA, Other Input = V_{DD} – 0.2 V/0.2 V		MIN	—	—	30	mA
				1 μs	—	3	—	
I_{DDS1}	Standby Current	$\overline{CE}$ = V_{IH}			—	—	3	mA
I_{DDS2}		$\overline{CE}$ = V_{DD} – 0.2 V, V_{DD} = 2.0 V~5.5 V	Ta = 25°C		—	1	—	μA
			Ta = –40~40°C		—	—	3	
			Ta = –40~85°C		—	—	20	

CAPACITANCE (Ta = 25°C, f = 1 MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C_{IN}	Input Capacitance	V_{IN} = GND	10	pF
C_{OUT}	Output Capacitance	V_{OUT} = GND	10	pF

Note: This parameter is periodically sampled and is not 100% tested.

AC CHARACTERISTICS AND OPERATING CONDITIONS ($Ta = -40°$ to $85°C$, $V_{DD} = 5\ V \pm 10\%$)

READ CYCLE

SYMBOL	PARAMETER	TC55NEM208AFPN/AFTN				UNIT
		55		70		
		MIN	MAX	MIN	MAX	
t_{RC}	Read Cycle Time	55	—	70	—	ns
t_{ACC}	Address Access Time	—	55	—	70	
t_{CO}	Chip Enable Access Time	—	55	—	70	
t_{OE}	Output Enable Access Time	—	30	—	35	
t_{COE}	Chip Enable Low to Output Active	5	—	5	—	
t_{OEE}	Output Enable Low to Output Active	0	—	0	—	
t_{OD}	Chip Enable High to Output High-Z	—	25	—	30	
t_{ODO}	Output Enable High to Output High-Z	—	25	—	30	
t_{OH}	Output Data Hold Time	10	—	10	—	

WRITE CYCLE

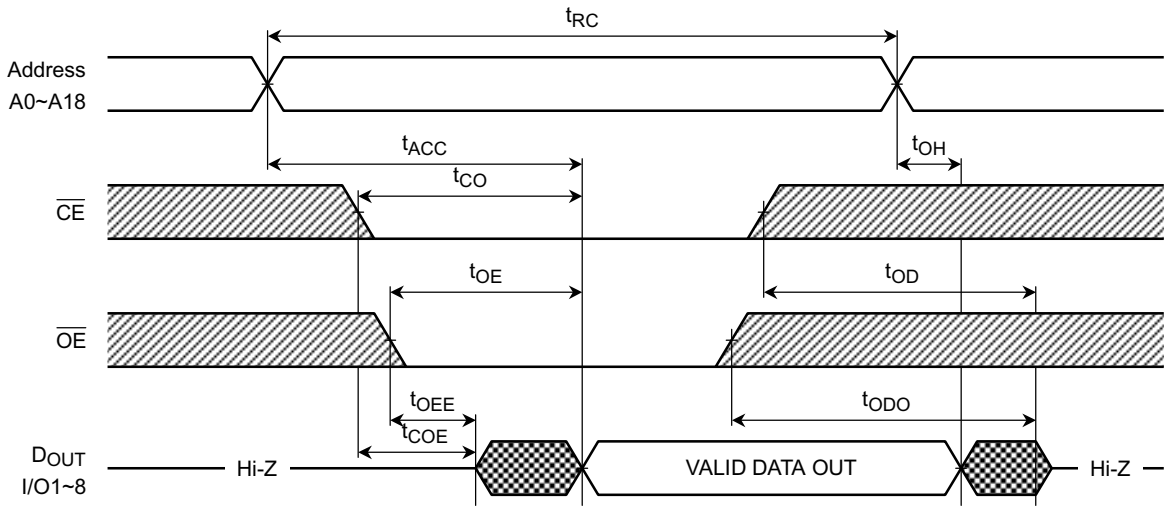
SYMBOL	PARAMETER	TC55NEM208AFPN/AFTN				UNIT
		55		70		
		MIN	MAX	MIN	MAX	
t_{WC}	Write Cycle Time	55	—	70	—	ns
t_{WP}	Write Pulse Width	40	—	50	—	
t_{CW}	Chip Enable to End of Write	45	—	55	—	
t_{AS}	Address Setup Time	0	—	0	—	
t_{WR}	Write Recovery Time	0	—	0	—	
t_{ODW}	R/W Low to Output High-Z	—	25	—	30	
t_{OEW}	R/W High to Output Active	0	—	0	—	
t_{DS}	Data Setup Time	25	—	30	—	
t_{DH}	Data Hold Time	0	—	0	—	

AC TEST CONDITIONS

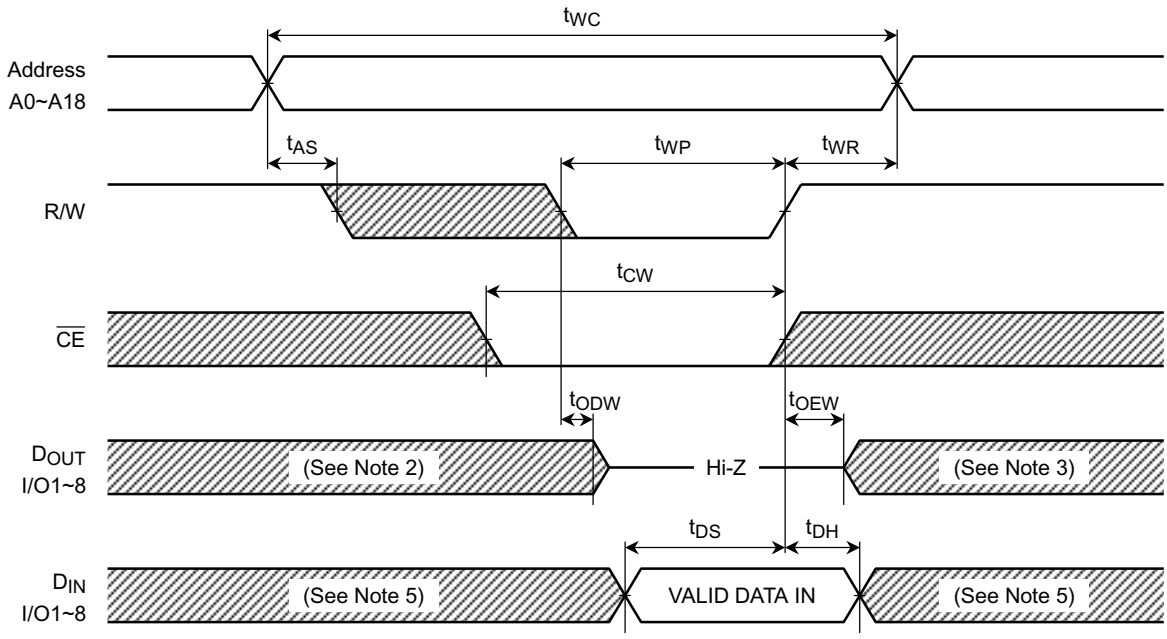
PARAMETER	TEST CONDITION
Output load	100 pF + 1 TTL Gate
Input pulse level	0.4 V, 2.4 V
Timing measurements	1.5 V
Reference level	1.5 V
t_R, t_F	5 ns

TIMING DIAGRAMS

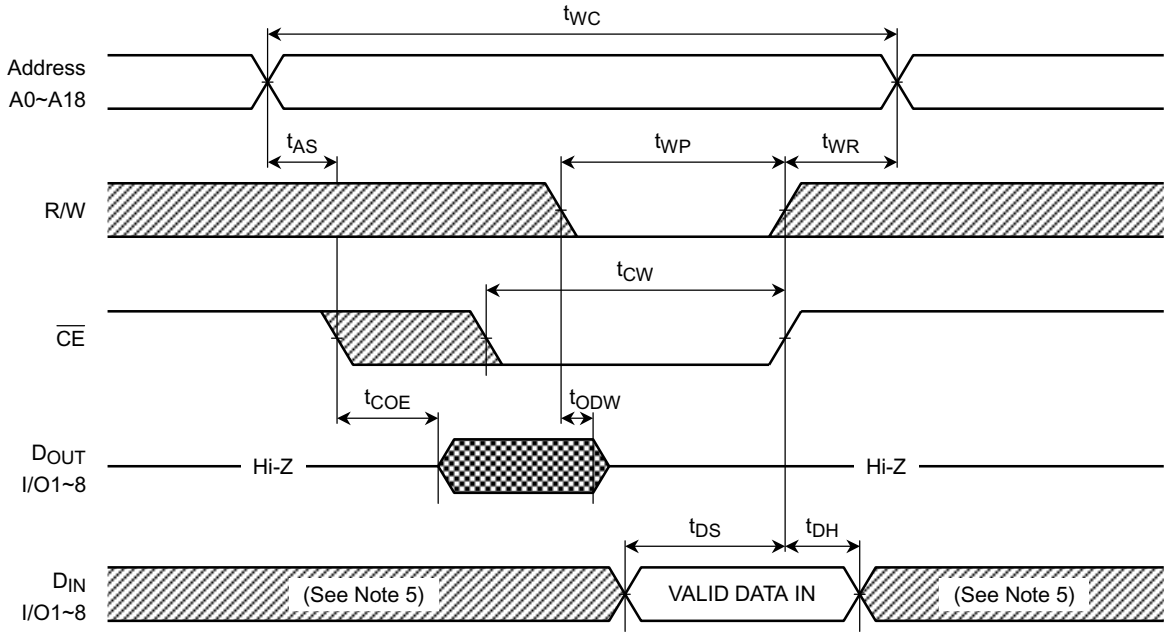
READ CYCLE (See Note 1)



WRITE CYCLE 1 (R/W CONTROLLED) (See Note 4)



WRITE CYCLE 2 ($\overline{CE}$ CONTROLLED) (See Note 4)



Note:

(1) R/W remains HIGH for the read cycle.

(2) If $\overline{CE}$ goes LOW coincident with or after R/W goes LOW, the outputs will remain at high impedance.

(3) If $\overline{CE}$ goes HIGH coincident with or before R/W goes HIGH, the outputs will remain at high impedance.

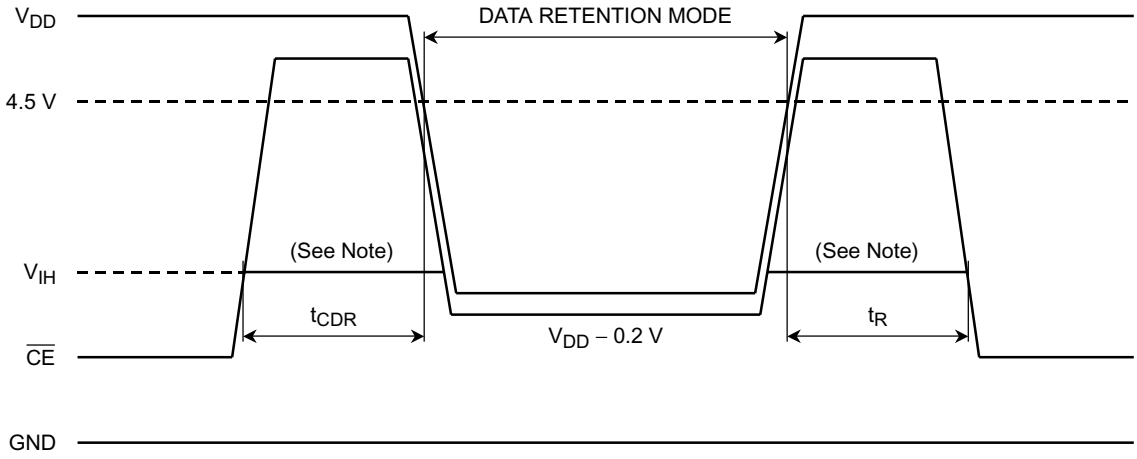
(4) If $\overline{OE}$ is HIGH during the write cycle, the outputs will remain at high impedance.

(5) Because I/O signals may be in the output state at this time, input signals of reverse polarity must not be applied.

DATA RETENTION CHARACTERISTICS (Ta = –40° to 85°C)

SYMBOL	PARAMETER		MIN	TYP	MAX	UNIT
V_{DH}	Data Retention Supply Voltage		2.0	—	5.5	V
I_{DDS2}	Standby Current	Ta = –40~40°C	—	—	3	µA
		Ta = –40~85°C	—	—	20	
t_{CDR}	Chip Deselect to Data Retention Mode Time		0	—	—	ns
t_R	Recovery Time		5	—	—	ms

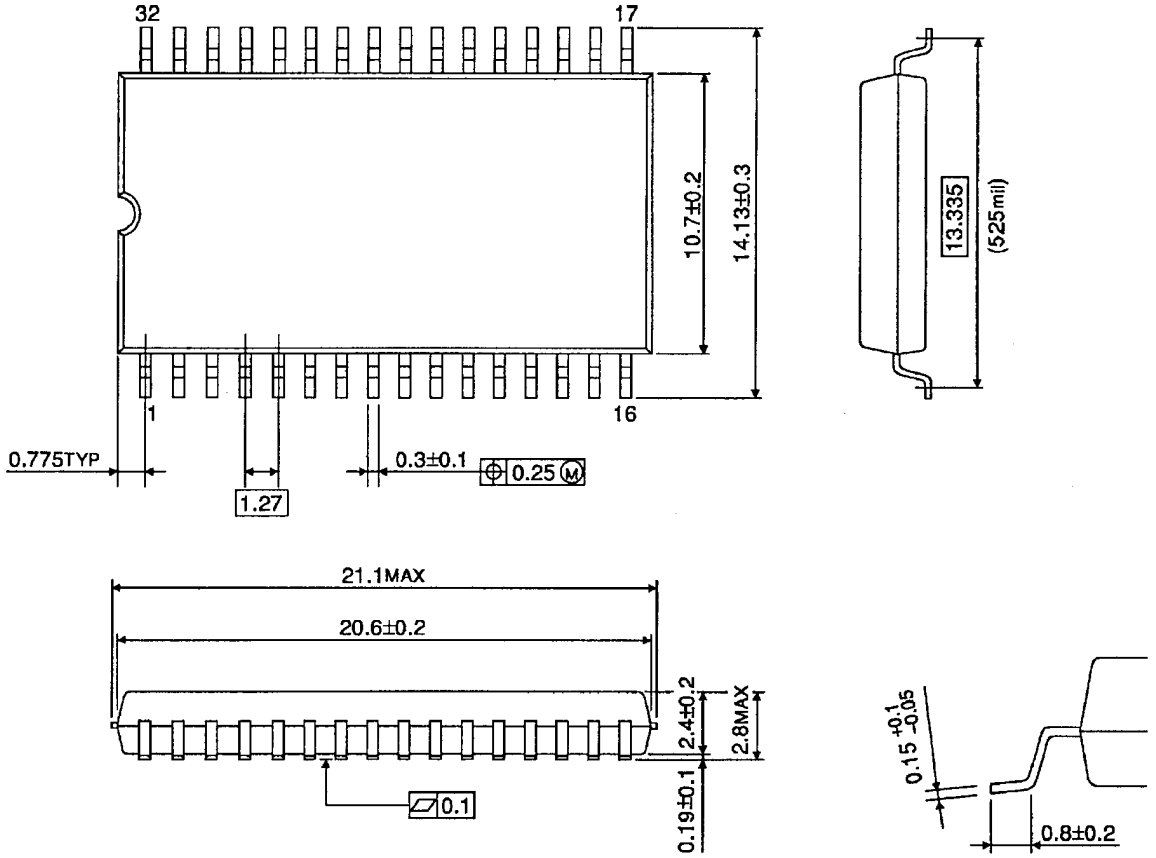
$\overline{CE}$ CONTROLLED DATA RETENTION MODE



Note: When $\overline{CE}$ is operating at the V_{IH} level (2.2V), the standby current is given by I_{DDS1} during the transition of V_{DD} from 4.5 to 2.4V.

PACKAGE DIMENSIONS

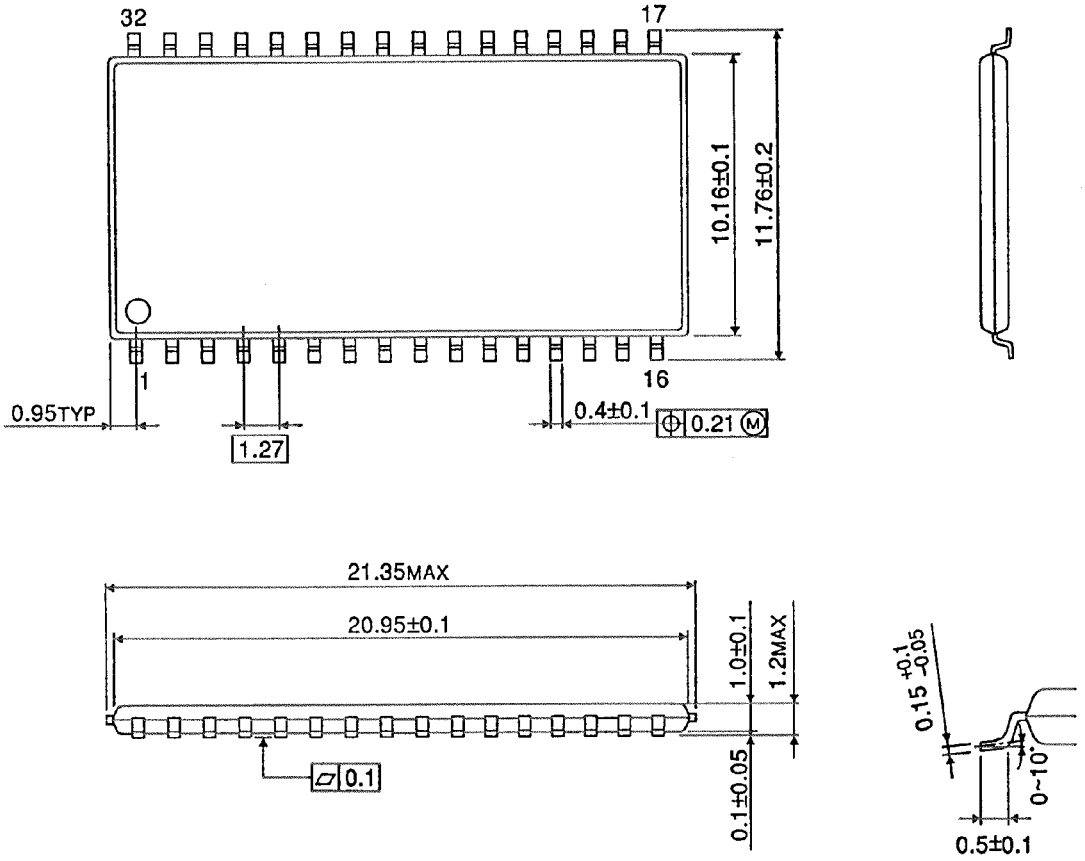
SOP32-P-525-1.27 Unit : mm



Weight: g (typ)

PACKAGE DIMENSIONS

TSOPII32-P-400-1.27 Unit: mm



Weight: g (typ)

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